



## **Applications**

**RTA (Rapid Thermal Annealing) RTO (Rapid Thermal Oxidation) Ohmic contact annealing** Implant annealing RTCVD of graphene and hBN Silicon carbonization RTCVD of poly silicon, SiO2, SiNx, ... The AS-Master system can process wafers up to 200 mm diameter at temperature up to 1450°C for the high temperature version.

The cold wall chamber technology provides significant advantages:

- Low memory effect
- Higher cooling rates
- Ultra clean environment

The cross lamp furnace with multi zone control insures enhanced temperature uniformity. Different furnace configurations are available depending on the application.

Pyrometer and thermocouple temperature measurements are standard features. The fast digital PID temperature controller provides accurate thermal control across the temperature range.

The AS-Master can receive a temperature controlled double quartz window and sample rotation to perform RTCVD processes.

Loadlock and cassette to cassette loading are optional features.

## **Optional features**

Graphite and silicon carbide coated susceptors Rough vacuum pump and turbo pump, automatic pressure control with throttle valve Fast cooling system, Selenization kits

## **Customer support**

Outstanding customer support for hardware, software and process Efficient remote support using software diagnostic capabilities High expertise in RTP processes of our process engineers Capability to support customer for process optimization

## **Physical specifications**

**Facilities** 

Voltage : 3x400V+N+Gr

Power: 75 kW, 90 kW or 105 kW

Water: 2 to 4 bars, pressure drop 1 bar, 30 to 50 l/mn

Compressed air: 6 bars (valve actuation)

Process gas fittings: double ferrule ¼ or VCR ¼ (option)

Dimensions and weight	Width	1,104 mm	43.5"
	Depth	1,550 mm	61.0"
	Height	2,500 mm	98.5"
	Mass	850 kg	1,874 lbs







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